

High Voltage Switching.

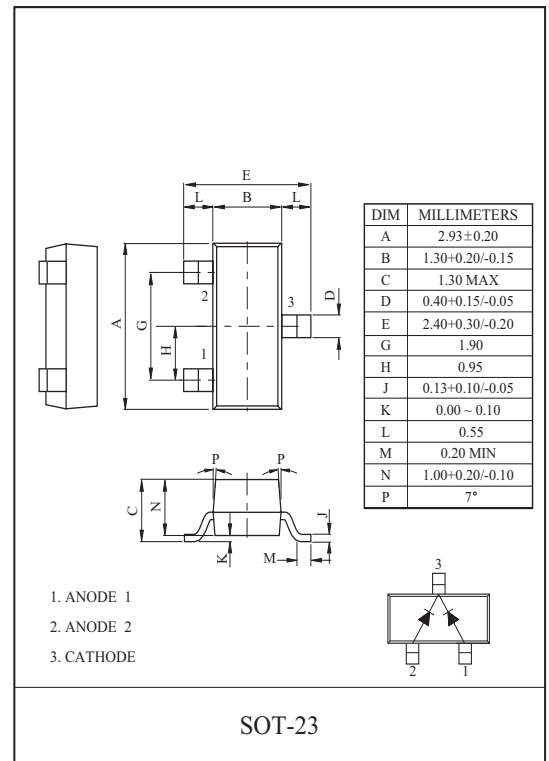
FEATURES

- Low Leakage Current.
- Repetitive Peak Reverse Voltage : V_{RRM} 250V.
- Low Capacitance : C_T 2pF.

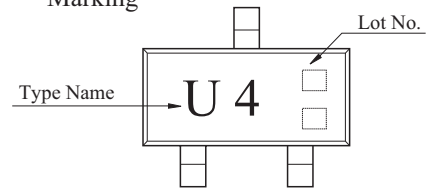
MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage		V_{RM}	250	V
Reverse Voltage		V_R	200	V
Maximum (Peak) Forward Current		I_{FM}	625	mA
Forward Current	Single diode loaded.	I_F	225	mA
	Double diode loaded.		125	
Surge Current (Square wave)	t = 1 μ s	I_{FSM}	9	A
	t = 100 μ s		3	A
	t = 10ms		1.7	A
Power Dissipation		P_D	250*	mW
Junction Temperature		T_j	150	
Storage Temperature Range		T_{stg}	-55 150	

Note : * Device mounted on a FR4 Printed-Circuit Board (PCB)



Marking



ELECTRICAL CHARACTERISTICS (Ta=25 °C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_F	$I_F=100mA$	-	-	1.0	V
		$I_F=200mA$	-	-	1.25	
Reverse Current	I_R	$V_R=200V$	-	-	0.1	μ A
		$V_R=200V, T_j=150$	-	-	100	
Total Capacitance	C_T	$V_R=0V, f=1MHz$	-	-	2	pF
Reverse Recovery Time	t_{rr}	$I_F=10mA, I_R=10mA, I_{RM}=1mA$	-	-	50	ns

BAV23C

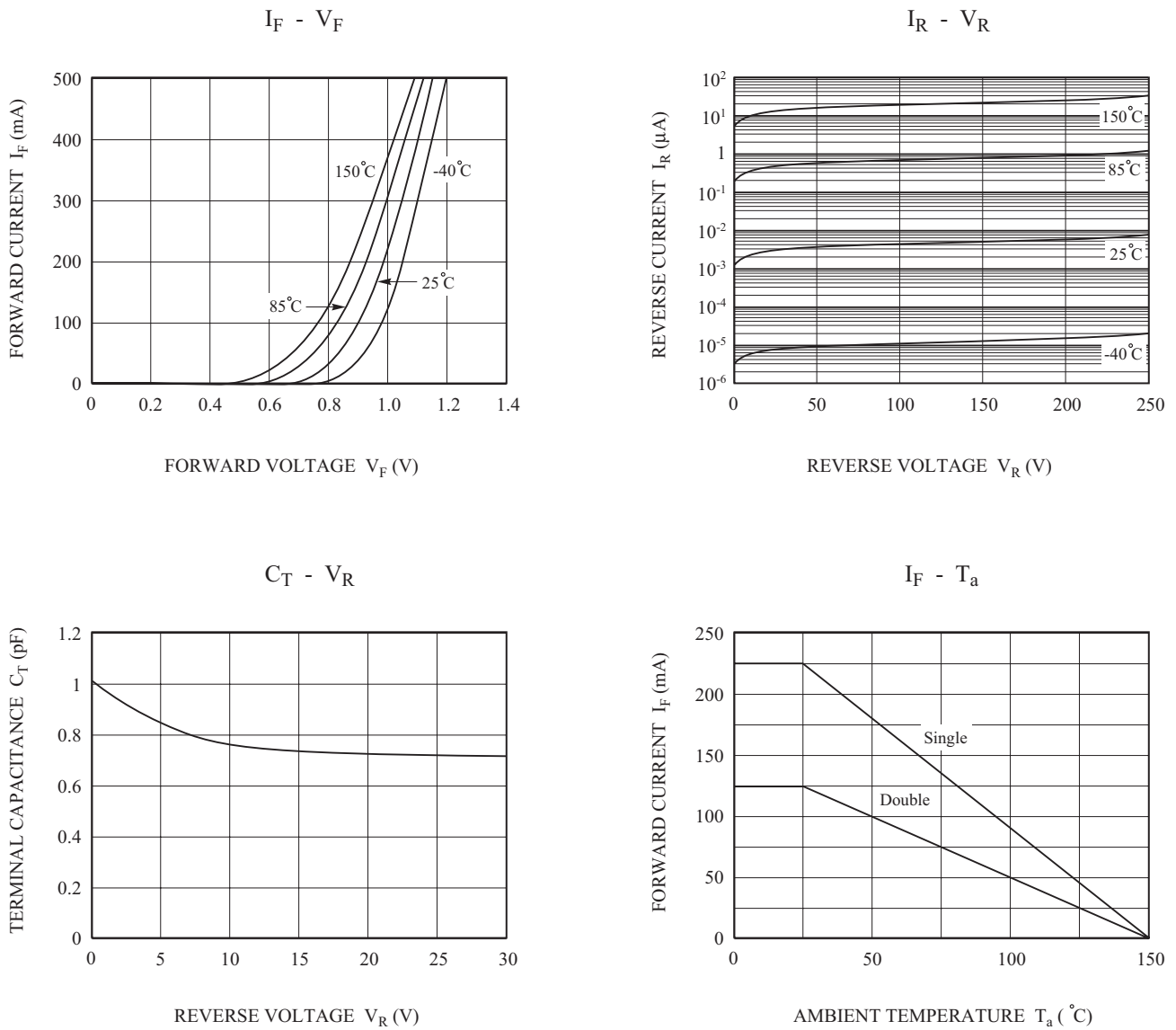


Fig. 1. REVERSE RECOVERY TIME(t_{rr}) TEST CIRCUIT

